
2SD789

Silicon NPN Epitaxial

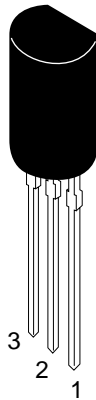
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Application

- Low frequency power amplifier
- Complementary pair with 2SB740

Outline

TO-92MOD



1. Emitter
2. Collector
3. Base

2SD789

Absolute Maximum Ratings (Ta = 25°C)

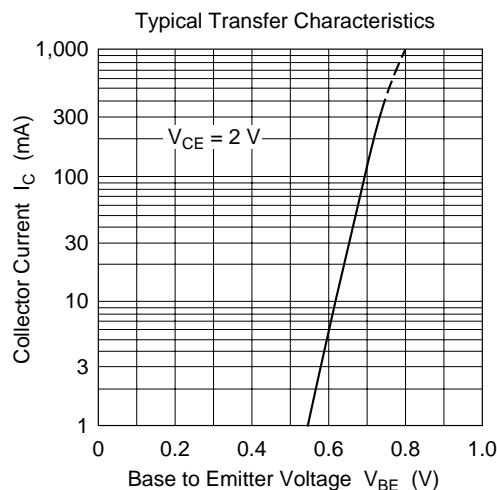
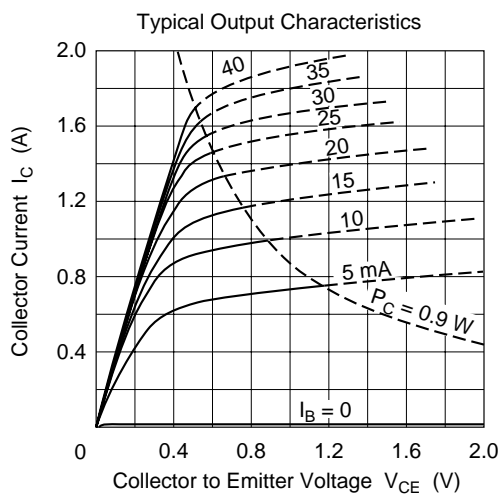
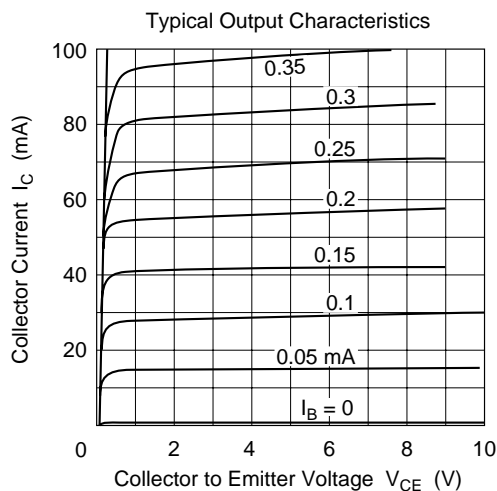
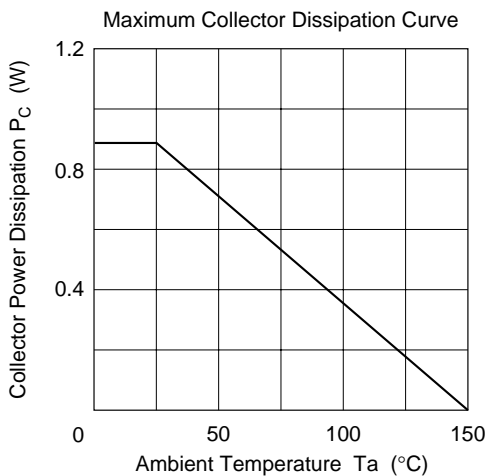
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	1	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

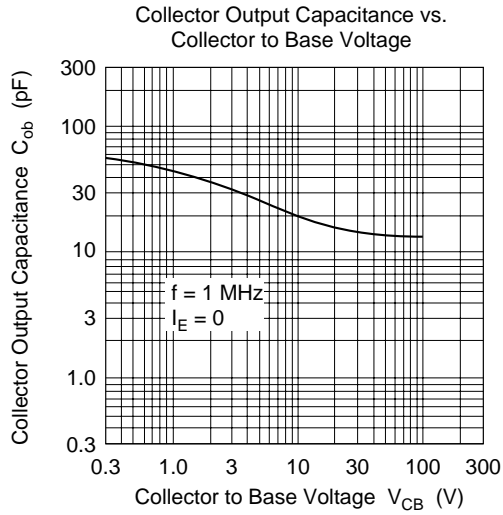
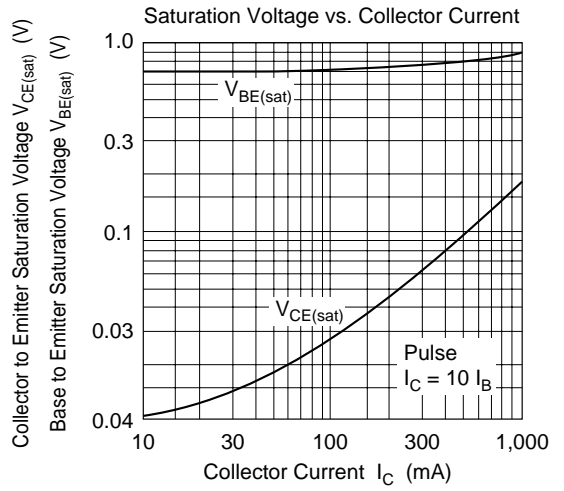
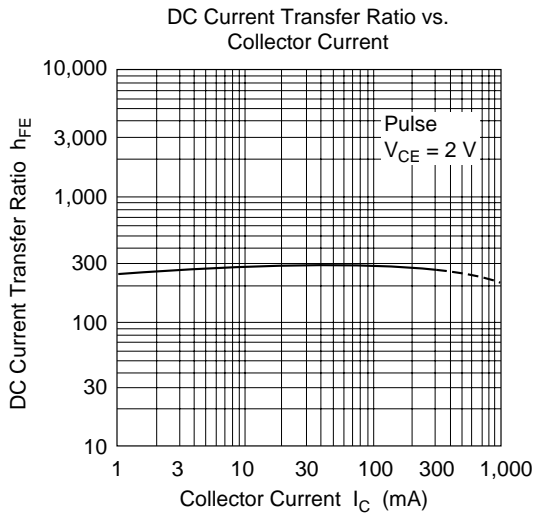
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	100	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1 mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 80 V, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.2	μA	$V_{EB} = 6 V, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	800		$V_{CE} = 2 V, I_C = 0.1 A$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 1 A, I_B = 0.1 A$
Gain bandwidth product	f_T	—	100	—	MHz	$V_{CE} = 2 V, I_C = 10 mA$
Collector output capacitance	C_{ob}	—	20	—	pF	$V_{CB} = 10 V, I_E = 0, f = 1MHz$

Note: 1. The 2SD789 is grouped by h_{FE} as follows.

B	C	D	E
100 to 200	160 to 320	250 to 500	400 to 800







Hitachi Code	TO-92 Mod
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.35 g

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